

AVTECH ELECTROSYSTEMS LTD.

NANOSECOND WAVEFORM ELECTRONICS
ENGINEERING - MANUFACTURING

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INSTRUCTIONS

MODEL AVX-S-IBM2-MI-MV-M BIAS TEE

S.N.:

WARRANTY

Avtech Electrosystems Ltd. warrants products of its manufacture to be free from defects in material and workmanship under conditions of normal use. If, within one year after delivery to the original owner, and after prepaid return by the original owner, this Avtech product is found to be defective, Avtech shall at its option repair or replace said defective item. This warranty does not apply to units which have been disassembled, modified or subjected to conditions exceeding the applicable specifications or ratings. This warranty is the extent of the obligation or liability assumed by Avtech with respect to this product and no other warranty or guarantee is either expressed or implied.

Fig. 1

BIAS INSERTION UNIT TEST ARRANGEMENT

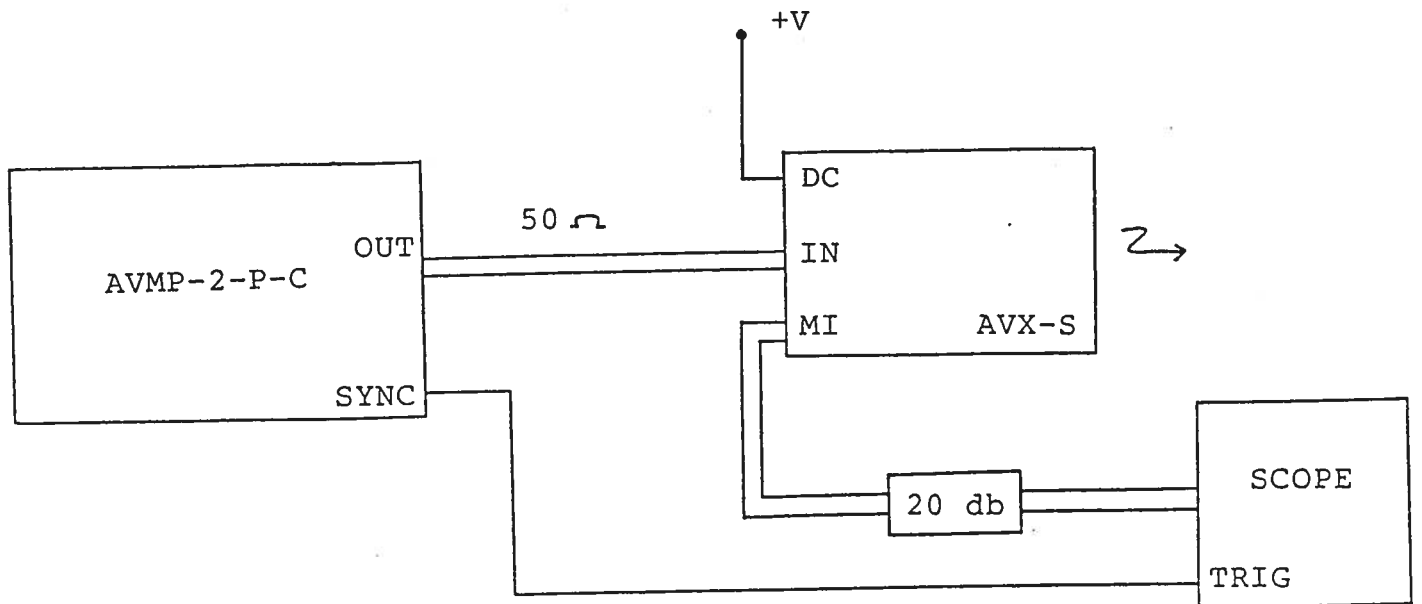
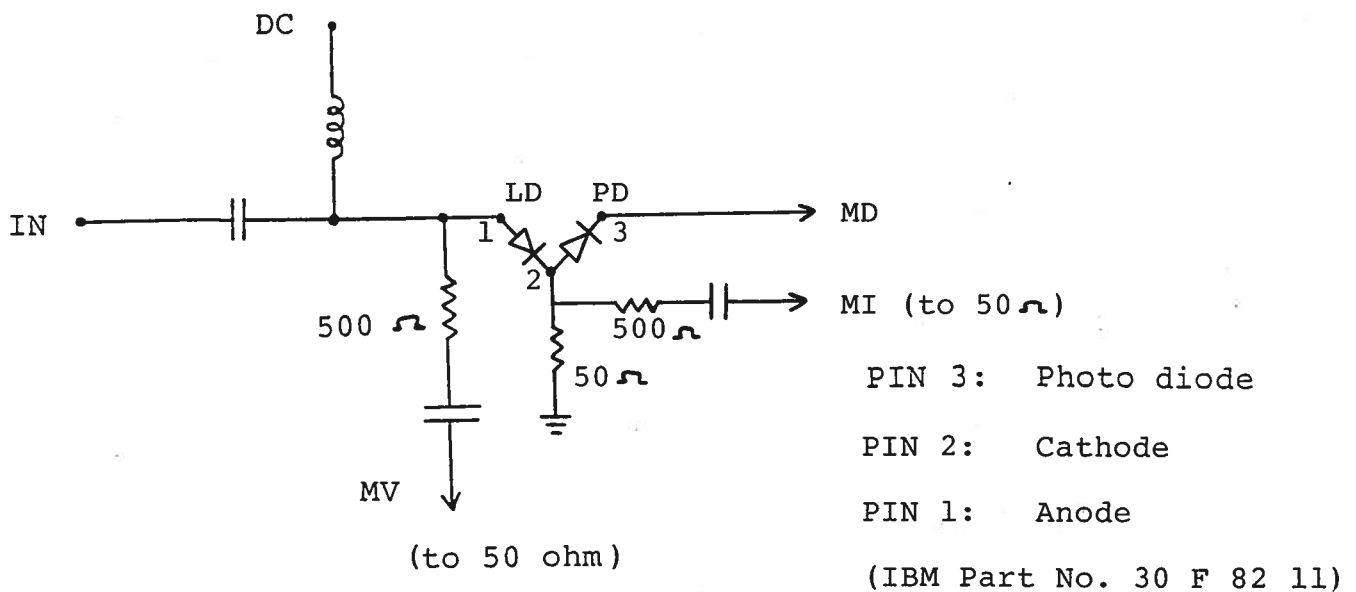


Fig. 2

FUNCTIONAL EQUIVALENT CIRCUIT



Notes:

- 1) The DC terminal of the bias insertion must either be shorted to ground (if a DC offset is not required) or a DC power supply must be applied. The laser diode will not function if the DC terminal is open circuited. Note that the DC current must not exceed ± 100 mA.
- 2) The MI port must be terminated into 50 ohms. Note that a 20 db (or larger) attenuator should be placed between the AVX-S MI output and the scope input since the MI output is very nearly equal to the amplitude of the input drive pulse.
- 3) The diode current I_D (Amps) and the MI output voltage are related as follows:

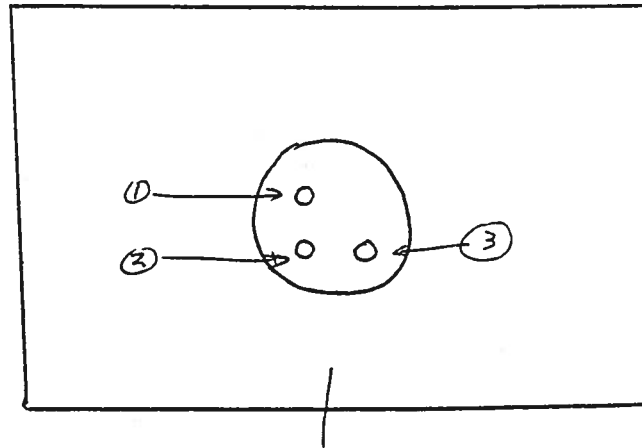
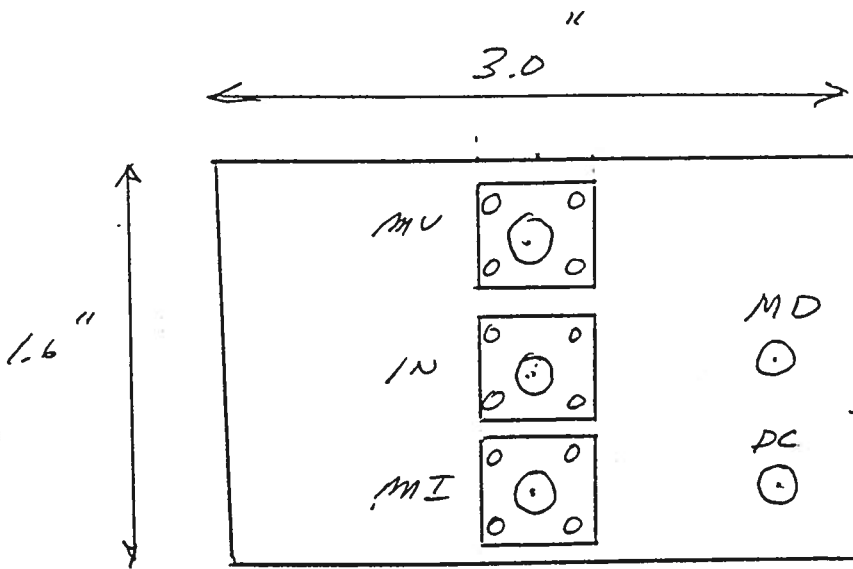
$$I_D = 0.2 MI$$

- 4) The MV output port also requires a 50 ohm termination. The voltage across the laser diode (V_D) is given by the following:

$$V_D = 10 (MV - MI)$$

where MV and MI are the voltages (into 50 ohms) at the MV and MI output ports.

- 5) The AVX-S input may be a sinusoid in the frequency range of 10 MHz to 1 GHz. For this mode of operation, a DC offset must be applied to the DC terminal.



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PAPER

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TELEX 053.4591

Fax No: 2617 Our Fax No: 613-226-2802

To: IBM Corp. Your Ref No: _____

914-894-3853 Our Ref: _____

Attn: John Ferrario Date: April 2, 1990

From: Avtech Electrosystems Ltd. Receivers Fax No: 914-894-6891

Subject: Quote - Laser Diode Bias Insertion Unit No. pages faxed: 3

With reference to your fax of March 13th, I am pleased to offer the following quotation for a special purpose laser diode bias insertion unit with TO 18 socket mounting.

Model designation: AVX-S-IBM2-MI-MV-M

Bandwidth: 10 MHz to 1 GHz.

Input impedance: 50 ohms (assumes a diode impedance of 5 ohms).

Input connector: SMA

Diode connector: TO 18 socket. Pin connections as per IBM Part No. 30F8211.

Photo diode output connector: Solder terminal.

Laser diode current monitor connector: SMA

Laser diode voltage monitor connector: SMA

DC bias: 0 to 100 mA. User applies required current to DC solder terminal.

Package size: 1.6" x 2.6" x 3.0" (see enclosed drawing).

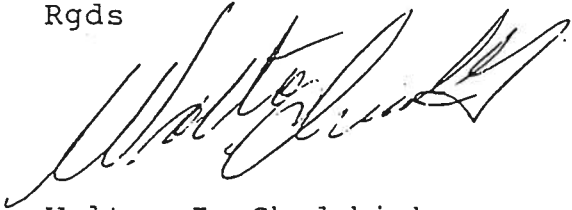
Functional equivalent circuit: See enclosed drawing.

Price: \$1290.00 U.S. each.
FOB: destination

Delivery: 60 days ARO

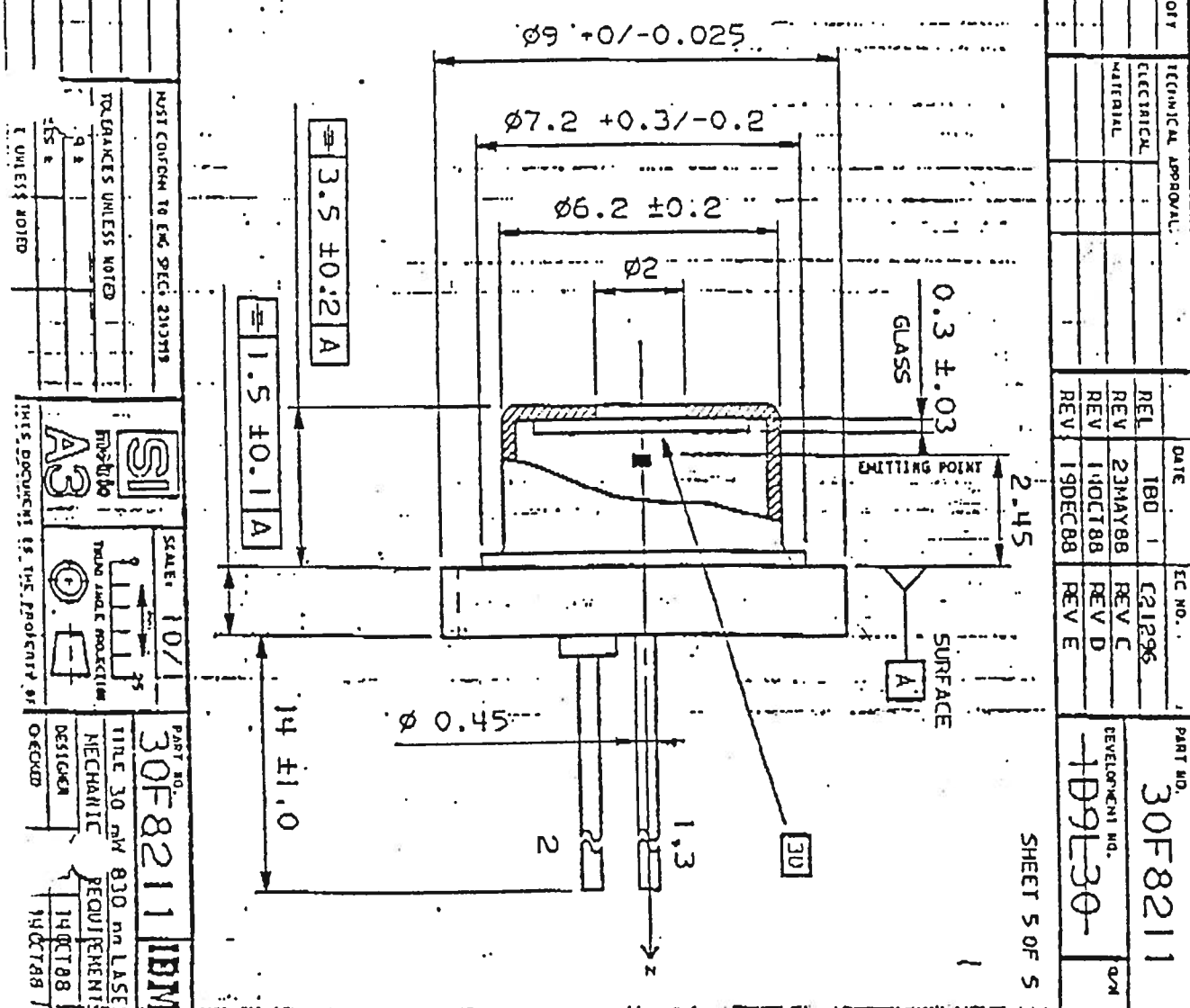
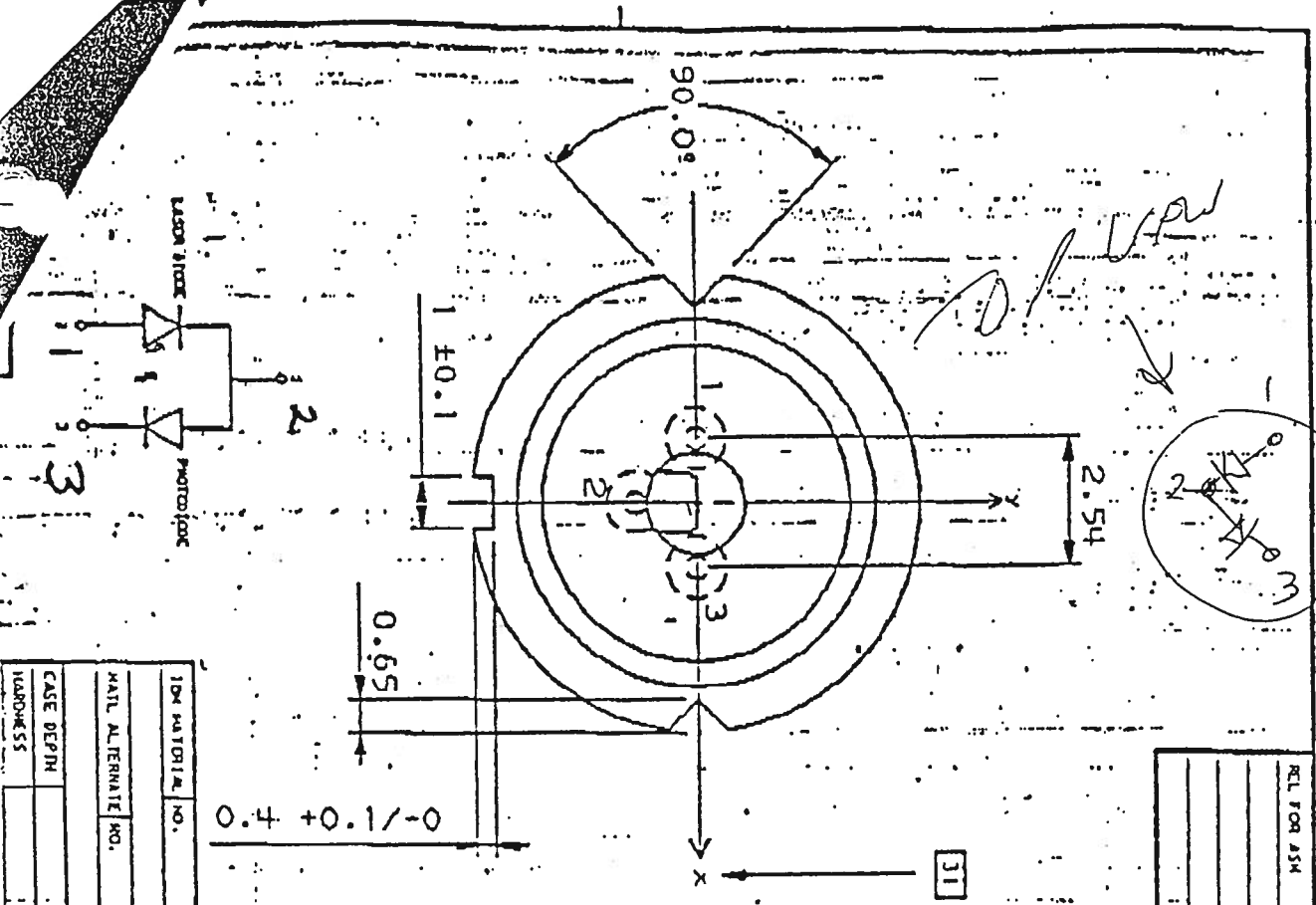
Thank you for your continuing interest in our products. Please call me again if you require any additional information or modification to the above quotation.

Rgds



Walter J. Chudobiak
Chief Engineer

WJC:sm



REL FOR ASM	QTY	TECHNICAL APPROVAL:	REL	DATE	EC NO.	PART NO.
		ELECTRICAL	180	180	C21296	30F8211
		MATERIAL	REV 2	23MAY98	REV C	DEVELOPMENT NO.
			REV 1	10OCT98	REV D	109L30-
			REV 1	19DEC98	REV E	

IBM MATERIAL NO.	MUST CONFORM TO ENG SPECS 210718	SCALE: 10/1	PART NO.
MATL ALTERNATE NO.	TOUGHNESS UNLESS NOTED	SI	30F8211
CASE DEPTH	ES B	IBM	IBM
TOLERANCES	UNLESS NOTED	THIS DOCUMENT IS THE PROPERTY OF	830 nm LASER REQUIREMENTS
			DESIGNER
			14 OCT 98
			19 OCT 98

SHEET 5 OF 5

08.09.90